

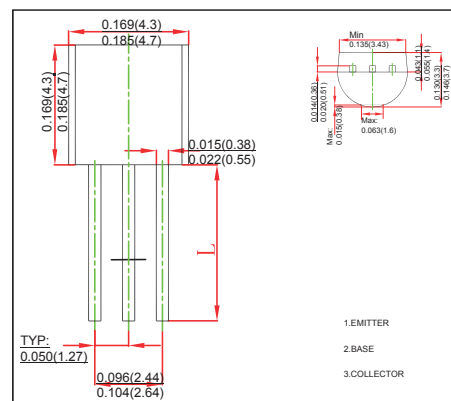
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Low collector Saturation Voltage: $V_{ce(sat)}=-0.3V(\text{Max})$
- Low Output Capacitance: $C_{ob}=4pF(\text{Typ.})$
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.15	A
Collector Power Dissipation	P_D	625	mW
Thermal Resistance from Junction to Ambient	R_{KJA}	200	°C /W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unia
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{EB}=-5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-2mA$	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.3	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-1mA$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		4	7	pF
Noise figure	NF	$V_{CE}=-6V, I_C=-0.1mA, f=1KHz, R_S=10K\Omega$			10	dB